Diode Semiconductor Device - Page 1 of 1



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In	closure Material:
GI	lass and metal
0	verall Length:
0.	340 inches
0	verall Diameter:
0.	187 inches
M	ounting Facility Quantity:
1	
M	ounting Method:
Te	erminal and threaded stud
Fe	eatures Provided:
He	ermetically sealed case
0	verall Width Across Flats:
0.	187 inches
Tł	nread Size:
0.	112 inches
Se	emiconductor Material:
Si	licon
Vo	oltage Rating In Volts Per Characteristic:
60	00.0 reverse voltage, peak
С	urrent Rating Per Characteristic:
12	2.00 amperes average forward current averaged over a full 60-hz cycle
M	aximum Operating Tempurature Per Measurement Point:
10	00.0 degrees celsius case
Tł	nread Series Designator:
Uı	nf
Te	erminal Type And Quantity:
1	threaded stud and 1 binding post
Sł	nelf Life:
N/	'a
Uı	nit Of Measure:
De	emilitarization:
No	0
Fi	ig:
A٢	110a0